Amendment Serial No. 10/825,816

IN THE CLAIMS:

- 1. (Currently Amended) A gain-clamped semiconductor optical amplifier comprising:
- a gain waveguide for amplifying an optical signal input to the gain waveguide; and
- a grating layer having a first and second gratings, the first grating on disposed at a first end portion of the grating layer, the first grating being disposed at a first end portion and the second grating disposed at a second end portion of the grating layer,

wherein the gain waveguide is disposed on the grating layer in a direct contact with the first grating and the first and second gratings have reflection factors different from each other.

- 2. (Canceled)
- 3. (Original) The gain-clamped semiconductor optical amplifier as claimed in claim 1, further comprising a clad laminated on the gain waveguide.
 - 4. (Canceled)
- 5. (Currently Amended) The gain-clamped semiconductor optical amplifier as claimed in claim 1. A gain-clamped semiconductor optical amplifier comprising:

 a gain waveguide for amplifying an optical signal input to the gain waveguide; and a grating layer having a first grating disposed at first end portion of the grating layer, wherein the gain waveguide is disposed on the grating layer in a direct contact with the first grating and the gain waveguide includes a mode conversion region formed at one end

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portion of the gain waveguide, the mode conversion region having a width which becomes narrower or wider as it goes to an end adjacent to the semiconductor optical amplifier.

- 6. (Original) The gain-clamped semiconductor optical amplifier as claimed in claim 5, wherein the mode conversion region is not in contact with the first grating.
- 7. (Original) The gain-clamped semiconductor optical amplifier as claimed in claim 5, wherein the mode conversion region is in contact with a portion of the first grating.
- 8. (Currently Amended) The gain-clamped semiconductor optical amplifier as claimed in claim[[2]]_I, wherein the gain waveguide includes mode conversion regions formed at both sides of the gain waveguide, the mode conversion regions having a width which becomes narrower or wider as it goes to a corresponding end of the semiconductor optical amplifier.
- 9. (Original) The gain-clamped semiconductor optical amplifier as claimed in claim 8, wherein the mode conversion regions are not in contact with the first and the second gratings.
- 10. (Original) The gain-clamped semiconductor optical amplifier as claimed in claim 8, wherein each of the mode conversion regions are in contact with a portion of a grating adjacent to the mode conversion region.
- 11. (Currently Amended) The guin-clamped semiconductor optical amplifier as claimed in claim 1, A gain-clamped semiconductor optical amplifier comprising:

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| a gain waveguide for amplifying an optical signal input to the gain waveguide; |
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| a grating layer having a first grating disposed at a first end portion of the grating layer; |
| <u>and</u> |
| non-reflection layers disposed on two portions of the semiconductor optical amplifier, |
| wherein the gain waveguide is disposed on the grating layer in a direct contact with the |
| first gratingfurther comprising non-reflection layers disposed on two portions of the |
| semiconductor optical amplifier. |

12. (Canceled)

| 13. (Original) The-gain clamped semiconductor optical amplifier as claimed in claim 1, |
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| further comprising: |
| anon reflection layer disposed on a first end surface of the semiconductor optical |
| amplifier, the first end surface serving as an input/output side of the semiconductor optical |
| emplifier; and |
| a high reflection layer-disposed on a second end surface of the semiconductor optical |
| amplifier A gain-clamped semiconductor optical amplifier comprising: |
| a gain waveguide for amplifying an optical signal input to the gain waveguide; |
| a grating layer having a first grating disposed at a first end portion of the grating layer; |
| a non-reflection layer disposed on a first end surface of the semiconductor optical |
| amplifier, the first end surface serving as an input/output side of the semiconductor optical |
| amplifier; and |

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| | a high reflection layer disposed on a second end surface of the semiconductor optical |
| | amplifier. |
| | wherein the gain waveguide is disposed on the grating layer in a direct contact with the |
| | first grating. |
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14-17. (Canceled)